BC856W-BC858W

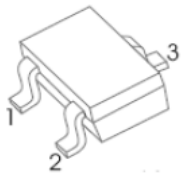
Plastic-Encapsulate Transistors

TRANSISTOR (PNP)

FEATURES

- Ideally suited for automatic insertion
- For Switching and AF Amplifier Applications

SOT-323



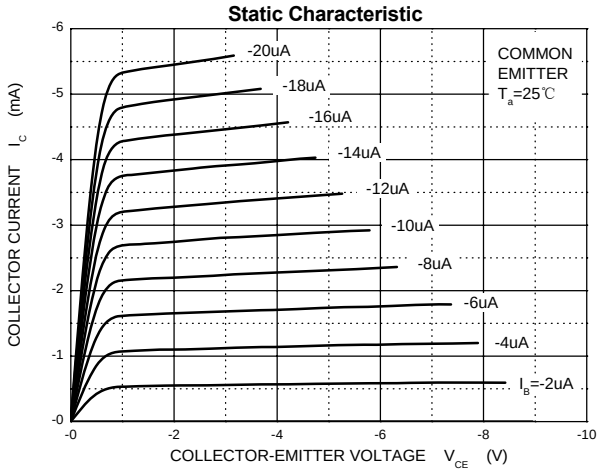
1. BASE
2. EMITTER
3. COLLECTOR

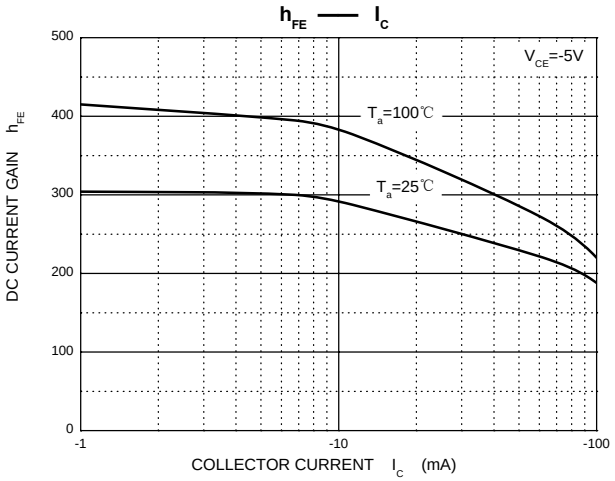
MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

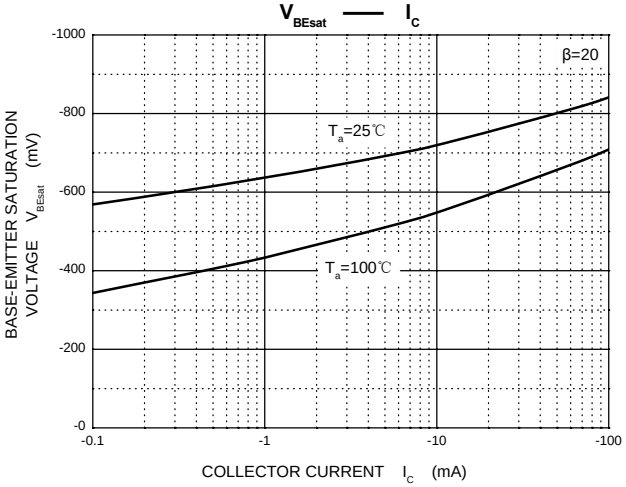
Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage		V
	BC856W	-80	
	BC857W	-50	
	BC858W	-30	
V_{CEO}	Collector-Emitter Voltage		V
	BC856W	-65	
	BC857W	-45	
	BC858W	-30	
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current –Continuous	-0.1	A
P_{C*}	Collector Power Dissipation	150	mW
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-65-150	℃

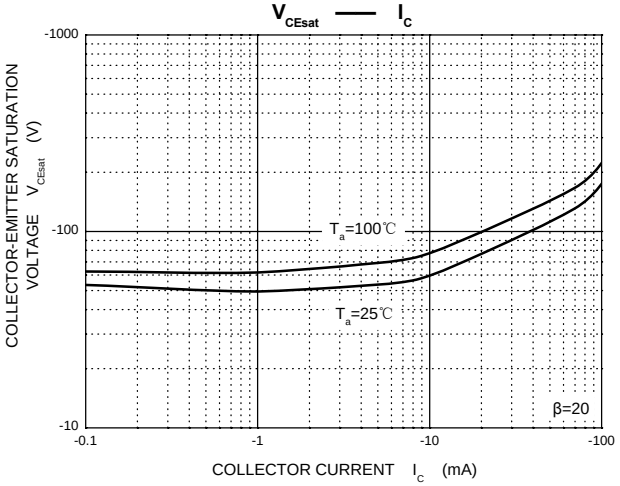
ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

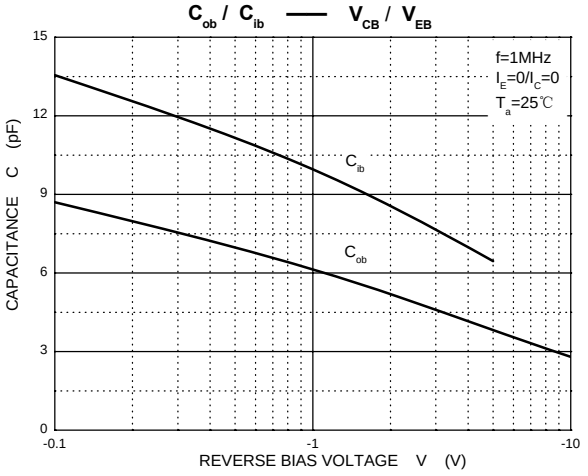
Parameter		Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	**BC856W**	V_{CBO}	I_C= -10μA, I_E=0	-80		V
	BC857W			-50		
	BC858W			-30		
Collector-emitter breakdown voltage	**BC856W**	V_{CEO}	I_C= -10mA, I_B=0	-65		V
	BC857W			-45		
	BC858W			-30		
Emitter-base breakdown voltage		V_{EBO}	I_E= -1μA, I_C=0	-5		V
Collector cut-off current		I_{CBO}	V_{CB}= -30 V , I_E=0		-15	nA
DC current gain	**BC856AW, 857AW,858AW**	h_{FE}	V_{CE}= -5V, I_C= -2mA	125	250	
	BC856BW, 857BW,858BW			220	475	
	BC857CW,BC858CW			420	800	
Collector-emitter saturation voltage		$V_{CE(sat)}$	I_C=-100mA, I_B= -5mA		-0.65	V
Base-emitter saturation voltage		$V_{BE(sat)}$	I_C= -100mA, I_B= -5mA		-1.1	V
Transition frequency		f_T	V_{CE}= -5V, I_C= -10mA f=100MHz	100		MHz
Collector capacitance		C_{ob}	V_{CB}=-10V, f=1MHz		4.5	pF

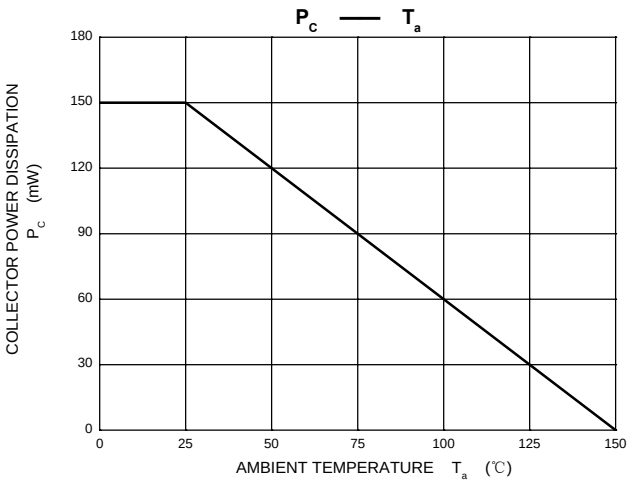

Static Characteristic
COMMON EMITTER
T_a=25℃
-20uA
-18uA
-16uA
-14uA
-12uA
-10uA
-8uA
-6uA
-4uA
I_B=-2uA
COLLECTOR CURRENT I_C (mA)
COLLECTOR-EMITTER VOLTAGE V_{CE} (V)


h_{FE} — I_C
V_{CE}=-5V
T_a=100℃
T_a=25℃
DC CURRENT GAIN h_{FE}
COLLECTOR CURRENT I_C (mA)


V_{BEsat} — I_C
β=20
T_a=25℃
T_a=100℃
BASE-EMITTER SATURATION VOLTAGE V_{BEsat} (mV)
COLLECTOR CURRENT I_C (mA)


V_{CEsat} — I_C
T_a=100℃
T_a=25℃
β=20
COLLECTOR-EMITTER SATURATION VOLTAGE V_{CEsat} (V)
COLLECTOR CURRENT I_C (mA)


C_{ob} / C_{ib} — V_{CB} / V_{EB}
f=1MHz
I_E=0/I_C=0
T_a=25℃
C_{ib}
C_{ob}
CAPACITANCE C (pF)
REVERSE BIAS VOLTAGE V (V)


P_C — T_a
COLLECTOR POWER DISSIPATION P_C (mW)
AMBIENT TEMPERATURE T_a (℃)

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads **SOT-323**

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